

COMPLEMENTARY POWER TRANSISTORS

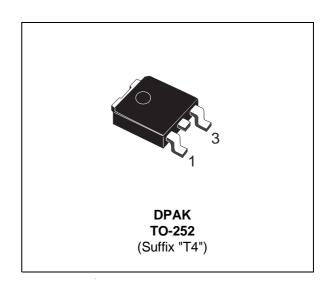
- STMicroelectronics PREFERRED SALESTYPES
- SURFACE-MOUNTING TO-252 (DPAK) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICALLY SIMILAR TO MJE2955T AND MJE3055T

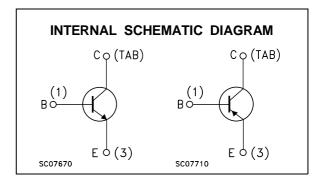
APPLICATIONS

 GENERAL PURPOSE SWITCHING AND AMPLIFIER

DESCRIPTION

The MJD2955 and MJD3055 form complementary PNP-NPN pairs. They are manufactured using Epitaxial Base technology for cost-effective performance.





ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit |
|------------------|--|-----|------------|------|
| | | NPN | MJD3055 | |
| | | PNP | MJD2955 | |
| V _{CBO} | Collector-Base Voltage (I _E = 0) | | 70 | V |
| V _{CEO} | Collector-Emitter Voltage (I _B = 0) | | 60 | V |
| V _{EBO} | Emitter-Base Voltage (I _C = 0) | | 5 | V |
| Ic | Collector Current | | 10 | Α |
| I_B | Base Current | | 6 | Α |
| P _{tot} | Total Dissipation at T _c = 25 °C | | 20 | W |
| T _{stg} | Storage Temperature | | -65 to 150 | °C |
| Tj | Max. Operating Junction Temperature | | 150 | °C |

For PNP type voltage and current values are negative.

February 2002 1/6

THERMAL DATA

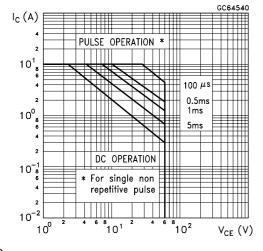
| R _{thj-case} | Thermal Resistance Junction-case | Max | 6.25 | °C/W |
|-----------------------|-------------------------------------|-----|------|------|
| R _{thj-amb} | Thermal Resistance Junction-ambient | Max | 100 | °C/W |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

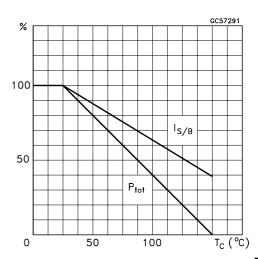
| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|------------------------|---|--|---------|------|----------|----------|
| I _{CEX} | Collector Cut-off Current (V _{BE} = -1.5 V) | $V_{CE} = 70 \text{ V}$ $V_{CE} = 70 \text{ V}$ $T_j = 150 ^{\circ}\text{C}$ | | | 20 2 | μA mA |
| I _{CBO} | Collector Cut-off Current (I _E = 0) | $V_{CB} = 70 \text{ V}$ $V_{CB} = 70 \text{ V}$ $T_j = 150 ^{\circ}\text{C}$ | | | 20 2 | μA mA |
| I _{CEO} | Collector Cut-off Current (I _B = 0) | V _{CE} = 30 V | | | 50 | μА |
| I _{EBO} | Emitter Cut-off Current (I _C = 0) | V _{EB} = 5 V | | | 0.5 | mA |
| V _{CEO(sus)*} | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 30 mA | 60 | | | V |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | $I_C = 4 \text{ A}$ $I_B = 0.4 \text{ A}$ $I_C = 10 \text{ A}$ $I_B = 3.3 \text{ A}$ | | | 1.1 8 | V V |
| V _{BE(on)} * | Base-Emitter Voltage | $I_C = 4 A$ $V_{CE} = 4 V$ | | | 1.8 | V |
| h _{FE} * | DC Current Gain | I _C = 4 A | 20 5 | | 100 | |
| f⊤ | Transition Frequency | Ic = 0.5 A V _{CE} = 10 V f = 500 KHz | 2 | | | MHz |

 $[\]ast$ Pulsed: Pulse duration = 300 $\mu s,$ duty cycle 1.5 %

Safe Operating Area

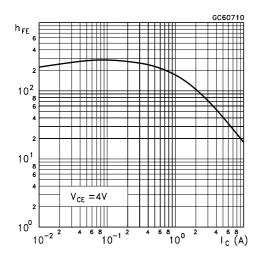


Derating Curves

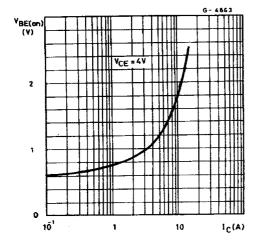


For PNP type voltage and current values are negative.

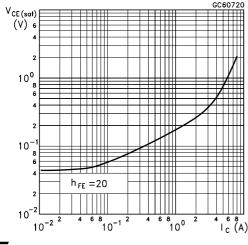
DC Current Gain (NPN type)



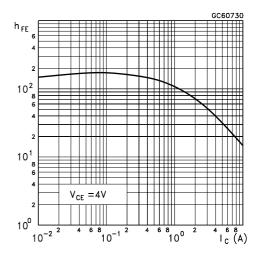
DC Transconductance (NPN type)



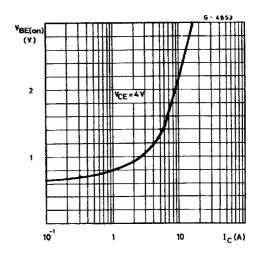
Collector-Emitter Saturation Voltage (NPN type)



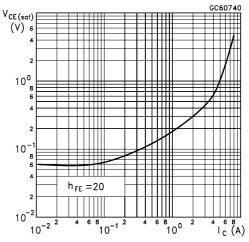
DC Current Gain (PNP type)



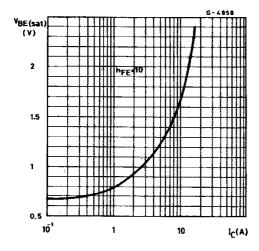
DC Transconductance (PNP type)



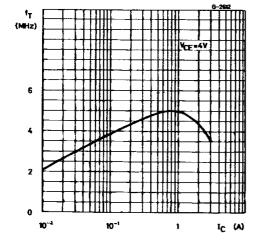
Collector-Emitter Saturation Voltage (PNP type)



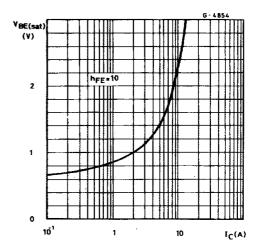
Base-Emitter Saturation Voltage (NPN type)



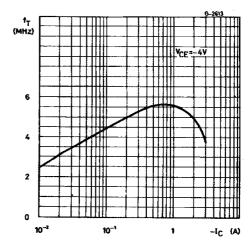
Transition Frequency (NPN type)



Base-Emitter Saturation Voltage (PNP type)

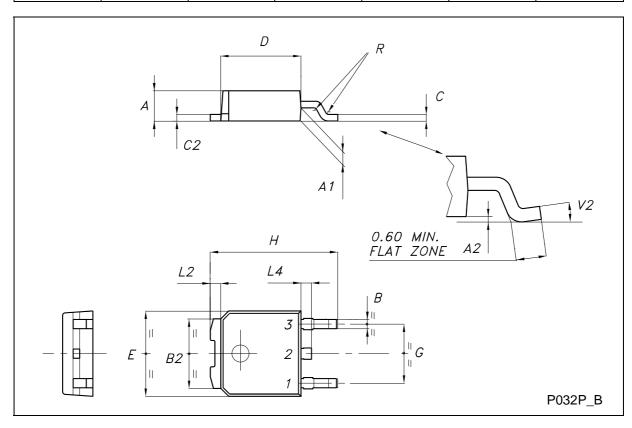


Transition Frequency (PNP type)



TO-252 (DPAK) MECHANICAL DATA

| DIM. | mm | | inch | | | |
|------|------|------|-------|-------|-------|-------|
| Diw. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| А | 2.20 | | 2.40 | 0.087 | | 0.094 |
| A1 | 0.90 | | 1.10 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| В | 0.64 | | 0.90 | 0.025 | | 0.035 |
| B2 | 5.20 | | 5.40 | 0.204 | | 0.213 |
| С | 0.45 | | 0.60 | 0.018 | | 0.024 |
| C2 | 0.48 | | 0.60 | 0.019 | | 0.024 |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 |
| Е | 6.40 | | 6.60 | 0.252 | | 0.260 |
| G | 4.40 | | 4.60 | 0.173 | | 0.181 |
| Н | 9.35 | | 10.10 | 0.368 | | 0.398 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.60 | | 1.00 | 0.024 | | 0.039 |
| V2 | 0° | | 8° | 0° | | 0° |



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